

Abstracts

A High Performance, Quasi-Monolithic 2 to 18 GHz Distributed GaAs FET Amplifier

A. Cappello, T. Alexander, J. Calviello, D. Ward, P. Bie and R. Pomian. "A High Performance, Quasi-Monolithic 2 to 18 GHz Distributed GaAs FET Amplifier." 1987 MTT-S International Microwave Symposium Digest 87.2 (1987 Vol. II [MWSYM]): 833-836.

Design, fabrication, and performance of a quasi-monolithic distributed GaAs FET amplifier is discussed. A gain of 20 dB and noise figure of 5.8 dB over 2 to 18 GHz are achieved. The amplifier circuits, using modified commercially available GaAs FET chips, are ideal for moderate volume (less than 5000), high performance applications.

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